



# Fast CMOS 3.3V 8-Bit Latched Transceiver

#### **Product Features**

- Functionally compatible with FCT3, LVT, and 74 series 543 families of products
- Tri-State outputs
- 5V Tolerant inputs and outputs
- 2.0V-3.6V Vcc supply operation
- Balanced sink and source output drives (24 mA)
- Low ground bounce outputs
- · Supports live insertion
- ESD Protection exceeds 2000V, Human Body Model 200V, Machine Model
- Packages available:
  - -24-pin 209-mil wide plastic SSOP (H)
  - -24-pin 173-mil wide plastic TSSOP(L)
  - -24-pin 150-mil wide plastic QSOP (Q)
  - -24-pin 300-mil wide plastic SOIC (S)

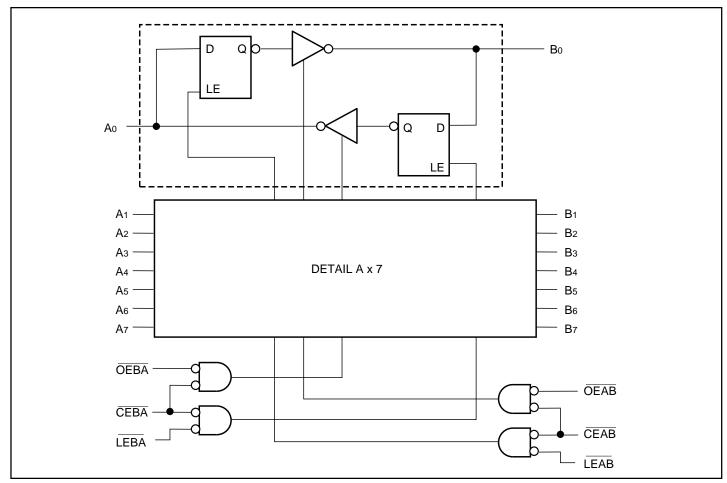
## **Product Description**

Pericom Semiconductor's PI74LCX series of logic circuits are produced in the Company's advanced 0.6 micron CMOS technology, achieving industry leading speed grades.

The PI74LCX543 is an 8-bit wide non-inverting transceiver designed with two sets of eight D-type latches with separate input and output controls for each set. For data flow from A to B, for example, the A-to-B Enable (CEAB) input must be LOW in order to enter data from A0–A7 or to take data from B0–B7, as indicated in the Truth Table. With CEAB LOW, a LOW signal makes the A-to-B latches transparent; a subsequent LOW-to-HIGH transition of the  $\overline{LEAB}$  signal puts the A latches in the storage mode and their outputs no longer change the A inputs. With  $\overline{CEAB}$  and  $\overline{OEAB}$  both LOW, the 3-state B output buffers are active and reflect the data present at the output of the A latches. Control of data from B to A is similar, but uses the CEAB,  $\overline{LEAB}$ , and OEAB inputs.

The PI74LCX543 can be driven from either 3.3V or 5.0V devices allowing this device to be used as a translator in a mixed 3.3/5.0V system.

#### **Logic Block Diagram**





# **Product Pin Configuration**

# **Product Pin Description**

Pin Name	Description
OEAB	A-to-B Output Enable Input (Active LOW)
ŌEBĀ	B-to-A Output Enable Input (Active LOW)
CEAB	A-to-B Enable Input (Active LOW)
CEBA	B-to-A Enable Input (Active LOW)
LEAB	A-to-B Latch Enable Input (Active LOW)
LEBA	B-to-A Latch Enable Input (Active LOW)
A0-A7	A-to-B Data Inputs or B-to-A 3-State Outputs
B0-B7	B-to-A Data Inputs or A-to-B 3-State Outputs
GND	Ground
Vcc	Power

# Truth Table (Non-Inverting)<sup>(1,2)</sup> For A-to-B (Symmetric with B-to-A)

Inputs			Latch Status	Output Buffers
CEAB	LEAB	<b>OEAB</b>	A-to-B	B0-B7
Н	X	X	Storing	High-Z
X	Н	X	Storing	_
X	X	Н		High Z
L	L	L	Transparent	Current A Inputs
L	Н	L	Storing	Previous* A Inputs

1. \*Before LEAB LOW-to-HIGH Transition

H = HIGH Voltage Level

L = LOW Voltage Level

X = Don't Care or Irrevelant

2. A-to-B data flow shown; B-to-A flow control is the same, except using CEBA, LEBA, and OEBA.



## **Maximum Ratings**

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature65°C to +150°C
Ambient Temperature with Power Applied—40°C to +85°C
Supply Voltage to Ground Potential (Inputs & Vcc Only)0.5V to +7.0V
Supply Voltage to Ground Potential (Outputs & D/O Only) -0.5V to +7.0V
DC Input Voltage0.5V to +7.0V
DC Output Current
Power Dissipation

#### Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## **Recommended Operating Conditions**

Symbol	Parameter	Min.	Max.	Units	
Vcc	Supply Voltage	Operating	2.0	3.6	
		Data Retention	1.5	3.6	
VI	Input Voltage		0	5.5	V
Vo	Output Voltage	HIGH or LOW State	0	Vcc	
		TRI-State	0	5.5	
Ioh/Iol	Output Current	Vcc = 3.0V-3.6V	_	±24	mA
		Vcc = 2.7V	_	±12	
TA	Free-Air Operating Temperature		-40	+85	°C
$\Delta t/\Delta V$	Input Edge Rate	V = 0.8V-2.0V, $Vcc = 3.0V$	0	10	ns/V



## **DC Electrical Characteristics** (Over the Operating Range, $T_A = -40$ °C to +85°C, $V_{CC} = 2.7$ V to 3.6V)

Parameters	Description	Test Conditions <sup>(1)</sup>	Min.	<b>Typ</b> <sup>(2)</sup>	Max.	Units	
VIH	Input HIGH Voltage	Guaranteed Logic HIGH Level		2.0	_	_	
VIL	Input LOW Voltage	Guaranteed Logic LOW Lev	vel	_	_	0.8	
Vон	Output HIGH Voltage	Vcc = 2.7-3.6	$V_{CC} = 2.7-3.6$ $I_{OH} = -0.1 \text{mA}$ $V_{CC} = 0.1 \text{mA}$		_	_	
		Vcc = 2.7	Iон = −12mA	2.2	_	_	
		Vcc = 3.0	Iон = −18mA	2.4	_	_	
			Iон = −24mA	2.2	_	_	V
Vol	Output LOW Voltage	Vcc = 2.7-3.6	Iol = 0.1mA	_	_	0.2	
		Vcc = 2.7	Iol = 12mA	_	_	0.4	
		Vcc = 3.0	Iol = 16mA	_	_	0.4	
			Iol = 24mA	_	_	0.55	
Vik	Clamp Diode Voltage	Vcc = Min., IiN = -18mA		_	-0.7	-1.2	
Iı	Input Leakage Current	$0 \le V_I \le 5.5V$	Vcc = 2.7-3.6	_	_	±5	
Ioz	Tri-State Output Leakage	$0 \le V_O \le 5.5V$ $V_I = V_{IH} \text{ or } V_{IL}$	Vcc = 2.7-3.6	_	_	±5	
Ioff	Power Down Disable	Vcc = 0V, Vin or Vout ≤ 5.5V		_	_	10	
Icc	Quiescent Power Supply Current	Vcc = Max.	V <sub>IN</sub> = GND or V <sub>CC</sub>	_	0.1	10	μΑ
ΔIcc	Quiescent Power Supply Current TTL Inputs HIGH	Vcc = Max.	$V_{\rm IN} = V_{\rm CC} - 0.6V^{(3)}$	_	_	500	

#### **Notes:**

- 1. For Max. or Min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type. 2. Typical values are at  $V_{\rm CC}=3.3V, +25^{\circ}C$  ambient.
- 3. Per TTL driven input; all other inputs at Vcc or GND.

# Capacitance

Parameters	Description	Test Conditions	Тур.	Units
Cin	Input Capacitance	Vcc = Open, VI = 0V or Vcc	7	
Соит	Output Capacitance	$V_{CC} = 3.3V$ , $V_I = 0V$ or $V_{CC}$	8	pF
Срд	Power Dissipation Capacitance	$V_{CC} = 3.3V$ , $V_I = 0V$ or $V_{CC}$ , $F = 10$ MHz	25	



# **Switching Characteristics over Operating Range**

			Vcc = 3	$3.3V \pm 0.3V$	Vcc	= 2.7V	
Parameters	Description	Conditions	Min.	Max.	Min.	Max.	Units
tPLH	Propagation Delay Transparent	CL = 50  pF	1.5	7.0	1.5	8.0	
tPHL tPLH tPHL	Mode An to Bn or Bn to An  Propagation Delay LEBA to An, LEAB to Bn	$R_L = 500\Omega$	1.5	8.5	1.5	9.5	_
tPZH tPZL	Output Enable Time OEBA or OEAB to An or Bn CEBA or CEAB to An or Bn		1.5	9.0	1.5	10.0	
tpzh tpzl	Output Disable Time <sup>(3)</sup> OEBA or OEAB to An or Bn CEBA or CEAB to An or Bn		1.5	7.0	1.5	7.5	ns
tsu	Setup Time, HIGH or LOW An or Bn to LEBA or LEAB		2.5	_	2.5	_	
tH	Hold Time, <u>HIGH</u> or <u>LOW</u> An or Bn to <u>LEBA</u> or <u>LEAB</u>		1.5	_	1.5	_	
tw	LEBA or LEAB Pulse Width LOW(3)		3.3	_	3.3	_	
tsk(o)	Output Skew <sup>(1)</sup>		_	1.0	_	_	

#### Note:

## **Dynamic Switching Characteristics** (TA = +25°C)

Parameters	Description	Test Conditions <sup>(1)</sup>	Тур.	Units
Volp	Dynamic LOW Peak Voltage	$V_{CC} = 3.3V, C_L = 50pF$	0.8	V
		$V_{IH} = 3.3V$ , $V_{IL} = 0V$		
Volv	Dynamic LOW Valley Voltage	$V_{CC} = 3.3V, C_L = 50pF$	0.8	V
		$V_{IH} = 3.3V$ , $V_{IL} = 0V$		

#### Note:

1. Measured with n-1 outputs switching from High-to-Low or Low-to-High. The remaining output is measured in the LOW state.

<sup>1.</sup> Skew between any two outputs, of the same package, switching in the same direction.